

30V, N-Channel NexFET™ Power MOSFETs

1 Features

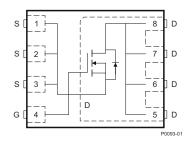
- Ultralow Q_g and Q_{gd}
- Low thermal resistance
- Avalanche rated
- Pb free terminal plating
- RoHS compliant
- Halogen Free
- SON 5mm × 6mm plastic package

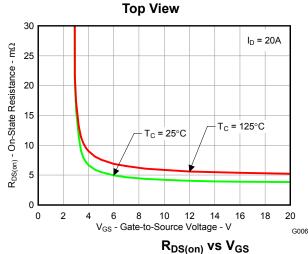
2 Applications

- Point-of-load synchronous buck in networking, telecom, and computing systems
- Optimized for control and synchronous FET applications

3 Description

The NexFET™ power MOSFET has been designed to minimize losses in power conversion applications.





Product Summary

V _{DS}	Drain to Source Voltage	30	V	
Qg	Gate Charge Total (4.5V)	6.4	nC	
Q _{gd}	Gate Charge Gate to Drain	1.9	nC	
	Drain to Source On Resistance	V _{GS} = 4.5V 5.4		mΩ
R _{DS(on)}	Drain to Source On Resistance	V _{GS} = 10V	4.1	mΩ
V _{GS(th)}	Threshold Voltage	1.5		V

Ordering Information

Device	Package	Media	Qty	Ship
CSD17510Q5A	SON 5mm × 6mm Plastic Package	13-Inch Reel	2500	Tape and Reel

Absolute Maximum Ratings

T _A = 2	5°C unless otherwise stated	VALUE	UNIT
V _{DS}	Drain to Source Voltage	30	V
V _{GS}	Gate to Source Voltage	±20	V
I _D	Continuous Drain Current, T _C = 25°C	55	Α
	Continuous Drain Current ⁽¹⁾	20	Α
I _{DM}	Pulsed Drain Current, T _A = 25°C ⁽²⁾	129	Α
P _D	Power Dissipation ⁽¹⁾	3	W
T _J , T _{STG}	Operating Junction and Storage Temperature Range	-55 to 150	°C
E _{AS}	Avalanche Energy, single pulse I_D = 54A, L = 0.1mH, R_G = 25 Ω	146	mJ

- Typical $R_{\theta JA} = 41^{\circ} \text{C/W} \text{ on } 1\text{-inch}^2 \text{ (6.45cm}^2\text{), 2oz. (0.071mm)}$ (1) thick) Cu pad on a 0.06-inch (1.52mm) thick FR4 PCB.
- Pulse duration ≤300µs, duty cycle ≤2%

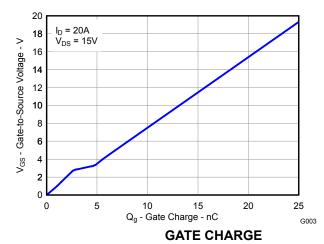




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4 Electrical Characteristics

(T_A = 25°C unless otherwise stated)

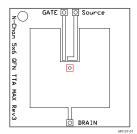
	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Static C	haracteristics				-	
BV _{DSS}	Drain to Source Voltage	V _{GS} = 0V, I _{DS} = 250μA	30			V
I _{DSS}	Drain to Source Leakage Current	V _{GS} = 0V, V _{DS} = 24V			1	μA
I _{GSS}	Gate to Source Leakage Current	V _{DS} = 0V, V _{GS} = 20V	,		100	nA
V _{GS(th)}	Gate to Source Threshold Voltage	$V_{DS} = V_{GS}$, $I_{DS} = 250\mu A$	1	1.5	2.1	V
	Drain to Source On Resistance	V _{GS} = 4.5V, I _{DS} = 20A		5.4	7.3	mΩ
R _{DS(on)}	Drain to Source On Resistance	V _{GS} = 10V, I _{DS} = 20A		4.1	5.2	mΩ
g _{fs}	Transconductance	V _{DS} = 15V, I _{DS} = 20A		59		S
Dynamic	c Characteristics		,		'	
C _{iss}	Input Capacitance			960	1250	pF
C _{oss}	Output Capacitance	$V_{GS} = 0V, V_{DS} = 15V,$ f = 1MHz	630 51		820	pF
C _{rss}	Reverse Transfer Capacitance	<i>j</i> - 1141112			66	pF
R _G	Series Gate Resistance			0.85	1.7	Ω
Qg	Gate Charge Total (4.5V)		,	6.4	8.3	nC
Q_{gd}	Gate Charge Gate to Drain	V 45V L 200		1.9		nC
Q _{gs}	Gate Charge Gate to Source	V _{DS} = 15V, I _{DS} = 20A		2.7		nC
Q _{g(th)}	Gate Charge at Vth		2.7 1.5			nC
Q _{oss}	Output Charge	V _{DS} = 13.5V, V _{GS} = 0V		16		nC
t _{d(on)}	Turn On Delay Time		,	7		ns
t _r	Rise Time	V _{DS} = 15V, V _{GS} = 4.5V,		11		ns
t _{d(off)}	Turn Off Delay Time	$I_{DS} = 20A, R_G = 2\Omega$		9		ns
t _f	Fall Time		4.1			ns
Diode C	haracteristics				1	
V _{SD}	Diode Forward Voltage	I _{SD} = 20A, V _{GS} = 0V		0.85	1	V
Q _{rr}	Reverse Recovery Charge	V = 42 5V L = 200 di/dt = 2000 free		25		nC
t _{rr}	Reverse Recovery Time	V _{DD} = 13.5V, I _F = 20A, di/dt = 300A/μs		24		ns

5 Thermal Characteristics

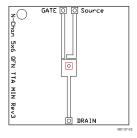
(T_A = 25°C unless otherwise stated)

	PARAMETER	MIN	TYP	MAX	UNIT
$R_{\theta JC}$	Thermal Resistance Junction to Case ⁽¹⁾			1.6	°C/W
$R_{\theta JA}$	Thermal Resistance Junction to Ambient ⁽¹⁾ (2)			51	°C/W

- (1) R_{θJC} is determined with the device mounted on a 1-inch² (6.45cm²), 2oz. (0.071mm thick) Cu pad on a 1.5-inch × 1.5-inch (3.81cm × 3.81cm), 0.06-inch (1.52mm) thick FR4 PCB. R_{θJC} is specified by design, whereas R_{θJA} is determined by the user's board design.
- (2) Device mounted on FR4 material with 1-inch² (6.45cm²), 2oz. (0.071mm thick) Cu.



 $\label{eq:maxRejA} \begin{array}{l} \mbox{Max RejJA} = 51 \mbox{°C/W} \\ \mbox{when mounted on 1 inch}^2 \\ \mbox{(6.45cm}^2) \mbox{ of 2oz. (0.071mm thick) Cu.} \end{array}$

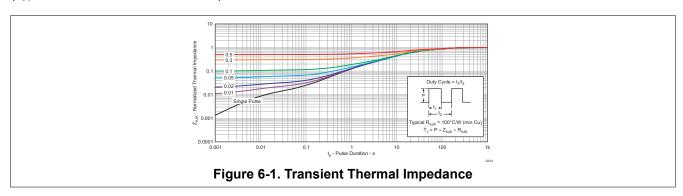


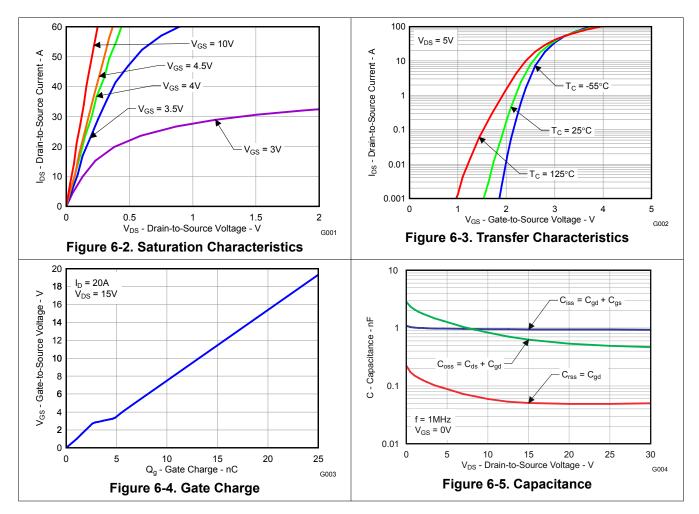
Max $R_{\theta JA}$ = 125°C/W when mounted on a minimum pad area of 2-oz. (0.071-mm thick) Cu.



6 Typical MOSFET Characteristics

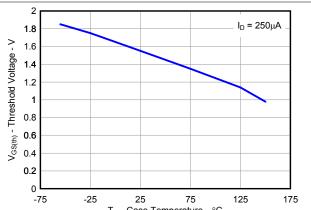
(T_A = 25°C unless otherwise stated)

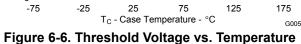




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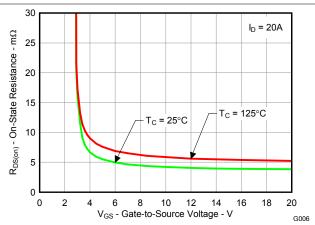


Figure 6-7. On-State Resistance vs. Gate-to-Source Voltage

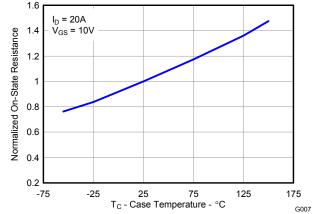


Figure 6-8. Normalized On-State Resistance vs.
Temperature

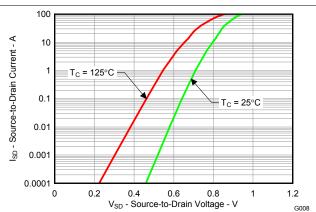


Figure 6-9. Typical Diode Forward Voltage

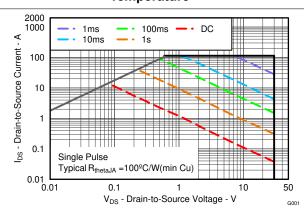


Figure 6-10. Maximum Safe Operating Area

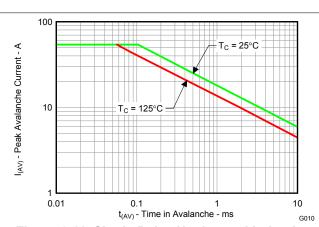
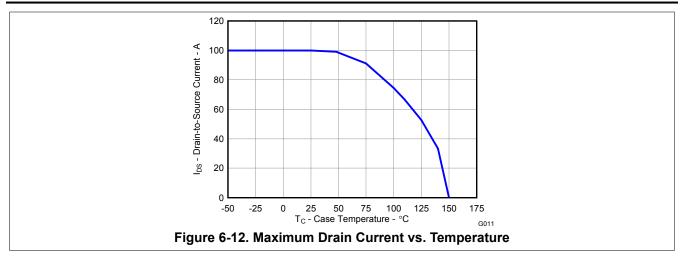


Figure 6-11. Single Pulse Unclamped Inductive Switching





7 Device and Documentation Support

TI offers an extensive line of development tools. Tools and software to evaluate the performance of the device, generate code, and develop solutions are listed below.

7.1 Third-Party Products Disclaimer

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7.2 Documentation Support

7.2.1 Related Documentation

7.3 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on ti.com. Click on Notifications to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

7.4 Support Resources

TI E2E™ support forums are an engineer's go-to source for fast, verified answers and design help — straight from the experts. Search existing answers or ask your own question to get the guick design help you need.

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7.5 Trademarks

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7.6 Electrostatic Discharge Caution



This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

7.7 Glossary

TI Glossary This glossary lists and explains terms, acronyms, and definitions.

8

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

Changes from Revision G (September 2012) to Revision H (December 2024)	Page
Updated the numbering format for tables, figures, and cross-references throughout the document	1

Changes from Revision * (July 2010) to Revision A ()

Page



 Changes from Revision F (October 2011) to Revision G (September 2012) Changed Figure 6-10 Changes from Revision E (July 2011) to Revision F (October 2011) Changed the I_D Continuous Drain Current, T_C = 25°C value From: 100A To: 55A Changed Figure 6-10 Changes from Revision A (August 2010) to Revision B () Changed R_{DS(on)} Test Conditions From V_{GS} = 8V To: V_{GS} = 10V 					
Changed Figure 6-10	4				
Changes from Revision E (July 2011) to Revision F (October 2011)	Page				
 Changed the I_D Continuous Drain Current, T_C = 25°C value From: 100A To: 55A 	1				
Changes from Revision A (August 2010) to Revision B ()	Page				
Changed R _{DS(on)} Test Conditions From V _{GS} = 8V To: V _{GS} = 10V	3 				
Changes from Revision B (September 2010) to Revision C ()	Page				
Absolute Maximum Ratings, changed the E _{AS} value from 45 to 146mJ	1				
Changes from Revision C (September 2010) to Revision D ()	Page				
Changes from Revision D (November 2010) to Revision E ()	Page				
 Changed V_{GS} in the Abs Max Ratings table From: +20/-12V To: ±20V Changed from +20/-12V to 20V 	1				



9 Mechanical Data

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Product Folder Links: CSD17510Q5A

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PACKAGING INFORMATION

Orderable part number	Status	Material type	Package Pins	Package qty Carrier	RoHS (3)	Lead finish/ Ball material	MSL rating/ Peak reflow	Op temp (°C)	Part marking (6)
CSD17510Q5A	Active	Production	VSONP (DQJ) 8	2500 LARGE T&R	ROHS Exempt	SN	Level-1-260C-UNLIM	-55 to 150	CSD17510
CSD17510Q5A.B	Active	Production	VSONP (DQJ) 8	2500 LARGE T&R	ROHS Exempt	SN	Level-1-260C-UNLIM	-55 to 150	CSD17510

⁽¹⁾ Status: For more details on status, see our product life cycle.

Multiple part markings will be inside parentheses. Only one part marking contained in parentheses and separated by a "~" will appear on a part. If a line is indented then it is a continuation of the previous line and the two combined represent the entire part marking for that device.

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⁽²⁾ Material type: When designated, preproduction parts are prototypes/experimental devices, and are not yet approved or released for full production. Testing and final process, including without limitation quality assurance, reliability performance testing, and/or process qualification, may not yet be complete, and this item is subject to further changes or possible discontinuation. If available for ordering, purchases will be subject to an additional waiver at checkout, and are intended for early internal evaluation purposes only. These items are sold without warranties of any kind.

⁽³⁾ RoHS values: Yes, No, RoHS Exempt. See the TI RoHS Statement for additional information and value definition.

⁽⁴⁾ Lead finish/Ball material: Parts may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

⁽⁵⁾ MSL rating/Peak reflow: The moisture sensitivity level ratings and peak solder (reflow) temperatures. In the event that a part has multiple moisture sensitivity ratings, only the lowest level per JEDEC standards is shown. Refer to the shipping label for the actual reflow temperature that will be used to mount the part to the printed circuit board.

⁽⁶⁾ Part marking: There may be an additional marking, which relates to the logo, the lot trace code information, or the environmental category of the part.

PACKAGE MATERIALS INFORMATION

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TAPE AND REEL INFORMATION





A0	Dimension designed to accommodate the component width
В0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

	Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	` '	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
ı	CSD17510Q5A	VSONP	DQJ	8	2500	330.0	12.4	6.3	5.3	1.2	8.0	12.0	Q1

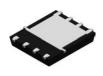
PACKAGE MATERIALS INFORMATION

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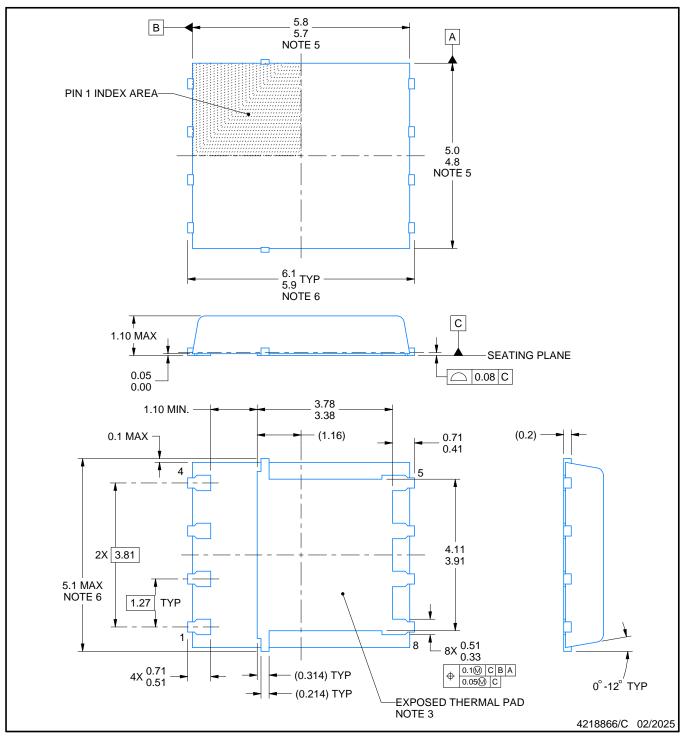


*All dimensions are nominal

Г	Device	Device Package Type		Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
	CSD17510Q5A	VSONP	DQJ	8	2500	340.0	340.0	38.0



PLASTIC SMALL OUTLINE - NO LEAD

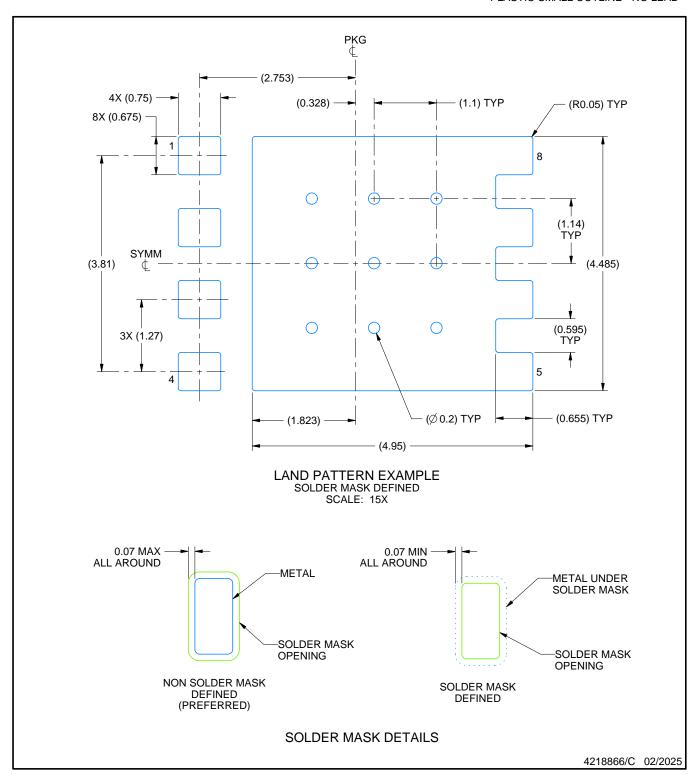


NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
- 2. This drawing is subject to change without notice.
- 3. The package thermal pad must be soldered to the printed circuit board for thermal and mechanical performance.
- Metalized features are supplier options and may not be on the package.
 These dimensions do not include mold flash protrusions or gate burrs.
- 6. These dimensions include interterminal flash or protrusion. Interterminal flash or protrusion shall not exceed 0.25 mm per side.



PLASTIC SMALL OUTLINE - NO LEAD

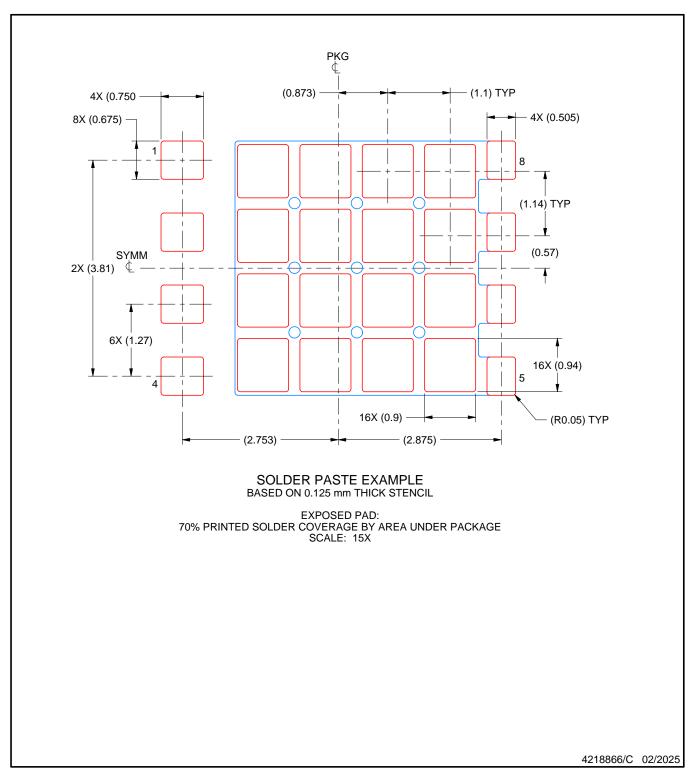


NOTES: (continued)

- 7. This package is designed to be soldered to a thermal pad on the board. For more information, see Texas Instruments literature number SLUA271 (www.ti.com/lit/slua271).
- 8. Vias are optional depending on application, refer to device data sheet. If some or all are implemented, recommended via locations are shown.



PLASTIC SMALL OUTLINE - NO LEAD



NOTES: (continued)

9. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.



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